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During production, some errors were introduced into the abstract. The correct version should read:

Effect of Off-Orientation of Seed Crystal on Silicon Carbide (SiC) Single-crystal Growth on the $(11\bar{2}0)$ Surface

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The effect of off-orientation growth has been investigated in terms of stacking fault formation during physical vapor transport (PVT) growth of silicon carbide (SiC) single crystals on the $(11\bar{2}0)$ seed crystal surface. Occurrence of stacking fault formation is largely dependent on the direction of off-orientation, and basal plane stacking fault density is significantly reduced by growing the crystals on a $(11\bar{2}0)$ seed crystal off-oriented toward $\langle 0001 \rangle$. The density of the basal plane stacking faults rapidly decreases from 100–150 cm^{−1} to ~10 cm^{−1} as the degree of off-orientation is increased from 0 to 10 deg. The results are interpreted in the framework of microscopic facet formation during PVT growth, and the introduction of off-orientation of seed crystal is assumed to prevent $(01\bar{1}0)$ and $(10\bar{1}0)$ microfacet formation on the $(11\bar{2}0)$ growing surface through modification of the surface growth kinetics and to suppress the stacking fault formation.

Key words: Silicon carbide, single crystal, sublimation growth, stacking fault